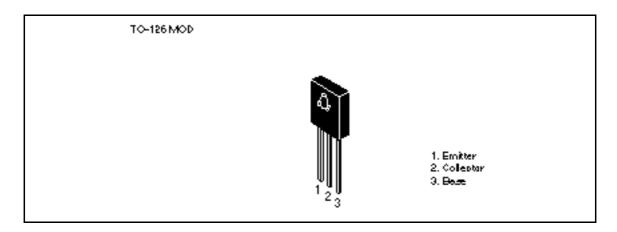
Silicon NPN Epitaxial

HITACHI

Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

		Ratings			
Item	Symbol	2SC1212	2SC1212A	 Unit	
Collector to base voltage	V_{CBO}	50	80	V	
Collector to emitter voltage	V_{CEO}	50	80	V	
Emitter to base voltage	V_{EBO}	4	4	V	
Collector current	I _c	1	1	А	
Collector power dissipation	P _c	0.75	0.75	W	
	P _C *1	8	8	W	
Junction temperature	Tj	150	150	°C	
Storage temperature	Tstg	-55 to +150	-55 to +150	°C	

Note: 1. Value at $T_c = 25^{\circ}C$

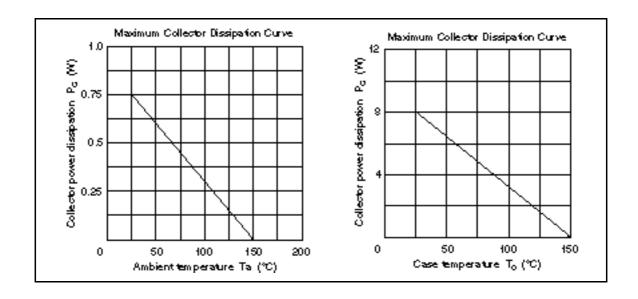


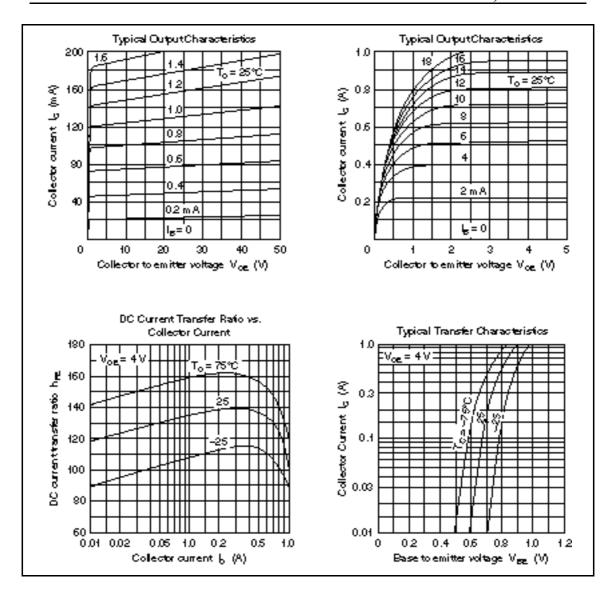
Electrical Characteristics ($Ta = 25^{\circ}C$)

		2SC1	212		2SC1212A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	50	_	_	80	_	_	V	$I_{c} = 1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	_	_	80	_	_	V	$I_{\rm C}$ = 10 mA, $R_{\rm BE}$ =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	_	_	4	_	_	V	$I_{E} = 1 \text{ mA}, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	5	_	_	5	μΑ	$V_{CB} = 50 \text{ V}, I_{E} = 0$
DC current tarnsfer ratio	h _{FE} *1	60	_	200	60	_	200		$V_{CE} = 4 \text{ V}, I_{C} = 50 \text{ mA}$
	h _{FE}	20	_	_	20	_	_		$V_{CE} = 4 \text{ V}, I_{C} = 1 \text{ A}$ (pulse test)
Base to emitter voltage	V_{BE}	_	0.65	1.0	_	0.65	1.0	V	$V_{CE} = 4 \text{ V}, I_{C} = 50 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.75	1.5	_	0.75	1.5	V	$I_C = 1 \text{ A}, I_B = 0.1 \text{ A}$ (pulse test)
Gain bandwidth product	f _T	_	160	_	_	160	_	MHz	$V_{CE} = 4 \text{ V}, I_{C} = 30 \text{ mA}$

Note: 1. The 2SC1212 and 2SC1212A are grouped by h_{FE} as follows.

В	С
60 to 120	100 to 200





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